

RELIABILITY REPORT
FOR
MAX308CSE+
PLASTIC ENCAPSULATED DEVICES

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MAXIM INTEGRATED

160 RIO ROBLES
SAN JOSE, CA 95134

Approved by
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Conclusion

The MAX308CSE+ successfully meets the quality and reliability standards required of all Maxim Integrated products. In addition, Maxim Integrated's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim Integrated's quality and reliability standards.

Table of Contents

I.Device Description	IV.Die Information
II.Manufacturing Information	V.Quality Assurance Information
III.Packaging Information	VI.Reliability Evaluation
.....Attachments	

I. Device Description**A. General**

The MAX308/MAX309 precision, monolithic, CMOS analog multiplexers (muxes) offer low on-resistance (less than 100 Ω), which is matched to within 5% between channels and remains flat over the specified analog signal range (7 V max). They also offer low leakage over temperature (NO-off leakage current less than 5nA at +85°C) and fast switching speeds (transition time less than 250ns). The MAX308 is a single-ended 1-of-8 device, and the MAX309 is a differential 2-of-4 device. The MAX308/MAX309 are fabricated with Maxim's improved 44V silicon-gate process. Design improvements yield extremely low charge injection (less than 10pC) and guarantee electrostatic discharge protection greater than 2000V. These muxes operate with a single +5V to +30V supply or bipolar $\pm 5V$ to $\pm 20V$ supplies, while retaining TTL/CMOS-logic input compatibility and fast switching. CMOS inputs provide reduced input loading. These improved parts are plug-in upgrades for the industry-standard DG408, DG409, DG508A, and DG509A.

II. Manufacturing Information

A. Description/Function:	Precision, 8-Channel/Dual 4-Channel, High-Performance, CMOS Analog Multiplexers
B. Process:	S5
C. Number of Device Transistors:	
D. Fabrication Location:	Oregon
E. Assembly Location:	Malaysia, Philippines, Thailand
F. Date of Initial Production:	Pre 1997

III. Packaging Information

A. Package Type:	16-pin SOIC (N)
B. Lead Frame:	Copper
C. Lead Finish:	100% matte Tin
D. Die Attach:	Conductive
E. Bondwire:	Au (1.3 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	#05-0301-0546
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C	Level 1
J. Single Layer Theta Ja:	115°C/W
K. Single Layer Theta Jc:	32°C/W
L. Multi Layer Theta Ja:	73°C/W
M. Multi Layer Theta Jc:	23°C/W

IV. Die Information

A. Dimensions:	80X136 mils
B. Passivation:	Si ₃ N ₄ /SiO ₂ (Silicon nitride/ Silicon dioxide)
C. Interconnect:	Al/0.5%Cu with Ti/TiN Barrier
D. Backside Metallization:	None
E. Minimum Metal Width:	5.0 microns (as drawn)
F. Minimum Metal Spacing:	5.0 microns (as drawn)
G. Bondpad Dimensions:	
H. Isolation Dielectric:	SiO ₂
I. Die Separation Method:	Wafer Saw

V. Quality Assurance Information

- A. Quality Assurance Contacts: Don Lipps (Manager, Reliability Engineering)
Bryan Preeshl (Vice President of QA)
- B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.
0.1% for all Visual Defects.
- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135C biased (static) life test are shown in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 160 \times 2} \quad (\text{Chi square value for MTTF upper limit})$$

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 6.87 \times 10^{-9}$$

$$\lambda = 6.87 \text{ F.I.T. (60\% confidence level @ 25°C)}$$

The following failure rate represents data collected from Maxim Integrated's reliability monitor program. Maxim Integrated performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at <http://www.maximintegrated.com/qa/reliability/monitor>. Cumulative monitor data for the S5 Process results in a FIT Rate of 0.09 @ 25C and 1.53 @ 55C (0.8 eV, 60% UCL)

B. E.S.D. and Latch-Up Testing (lot NSXAG9294A, D/C 0047)

The AG56 die type has been found to have all pins able to withstand a HBM transient pulse of +/-2500V per Mil-Std 883 Method 3015.7. Latch-Up testing has shown that this device withstands a current of +/-250mA.

Table 1
Reliability Evaluation Test Results

MAX308CSE+

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES	COMMENTS
Static Life Test (Note 1)	Ta = 135°C	DC Parameters	80	0	NSXAGA373C, D/C 0117
	Biased	& functionality	80	0	NSXAFA352C, D/C 0101
	Time = 192 hrs.				

Note 1: Life Test Data may represent plastic DIP qualification lots.